

**Alois Krost**

**“Metalorganic Vapour Phase Epitaxy of GaN on Si: from Principles to Devices”**



Alois Krost was educated in physics at RWTH Aachen where he reached a Doctoral degree in 1981 on Hot Wall Epitaxy of  $V_2VI_3$  compounds. From 1983 to 1998 he has been the head of the department of material science at TU Berlin working on growth and characterization of different semiconductors such as semimagnetic II-VI, InP on Si, InGaAs-based laser structures on InP, or InAs-based quantum dots on GaAs by MOCVD.

In 1998 he was appointed a full professorship for Semiconductor Epitaxy at the Otto-von-Guericke University, Magdeburg. Currently, his main interest is MOCVD growth and characterization of wide band gap semiconductors GaN-on-Si, and ZnO. Especially, he and his group have pioneered GaN-on-silicon as a cheap alternative to conventional sapphire and SiC substrates. A special interest is on advanced x-ray characterization methods including depth resolved grazing incidence diffraction. He authored or co-authored more than 350 papers and book articles, and 36 patents and patent applications. Alois Krost is a member of the German Physical Society, MRS, and SPIE.